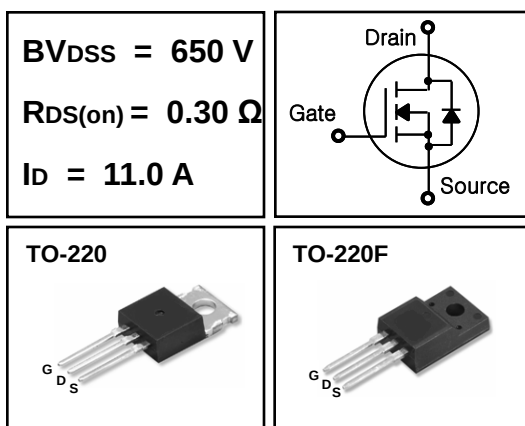


PFP65T360 / PFF65T360

N-Channel Super Junction MOSFET

FEATURES

- ❑ New technology for high voltage device
- ❑ Low $R_{DS(on)}$ low conduction losses
- ❑ Small package
- ❑ Ultra low gate charge cause lower driving requirement
- ❑ 100% avalanche tested
- ❑ RoHS



APPLICATION

- ❑ Power Factor Correction(PFC)
- ❑ Switched mode power supply (SMPS)
- ❑ Uninterruptible Power Supply (UPS)

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	PFP65T360	PFF65T360	Units
V_{DS}	Drain-Source Voltage ($V_{GS}=0\text{V}$)	650		V
I_D	Drain Current – Continuous ($T_c = 25^\circ\text{C}$)	11.0	11.0*	A
	Drain Current – Continuous ($T_c = 100^\circ\text{C}$)	7.0	7.0*	A
$I_{DM}(\text{pulse})$	Drain Current – Pulsed * Note 1	46	46*	A
V_{GS}	Gate-Source Voltage ($V_{DS}=0\text{V}$)	± 30		V
E_{AS}	Single Pulsed Avalanche Energy * Note 2	144		mJ
I_{AR}	Avalanche Current * Note 1	6		A
E_{AR}	Repetitive Avalanche Energy * Note 1	0.5		mJ
dv/dt	Drain Source Voltage Slope, $V_{DS} \leq 480\text{V}$	50		V/ns
	Reverse Diode dv/dt , $V_{DS} \leq 480\text{V}$	15		V/ns
P_D	Maximum Power Dissipation ($T_c = 25^\circ\text{C}$)	101	32.6	W
	Derate above 25°C	0.81	0.26	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$

* Limited by maximum junction temperature

Thermal Resistance Characteristics

Symbol	Parameter	PFP65T360	PFF65T360	Units
$R_{\theta JC}$	Junction-to-Case (Maximum)	1.24	3.83	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient (Maximum)	62	80	

Electrical Characteristics $T_A=25\text{ }^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 uA	3.0	3.5	4.0	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 7.0 A	--	300	360	m.ohm
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 uA	650	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	--	--	1	uA
		V _{DS} = 650 V, T _C =125 °C	--	--	100	uA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
Dynamic Characteristics						
g _{FS}	Forward Transconductance	V _{DS} = 20V, I _D = 7.0A	--	8	--	S
R _G	Intrinsic Gate Resistance	f = 1.0 MHz, open drain	--	36	--	ohm
C _{iss}	Input Capacitance	V _{DS} = 50 V, V _{GS} = 0 V, f = 1.0 MHz	--	1285	1450	pF
C _{oss}	Output Capacitance		--	45	60	pF
C _{rss}	Reverse Transfer Capacitance		--	3.5	6	pF
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 11.5 A, V _{GS} = 10 V	--	24	30	nC
Q _{gs}	Gate-Source Charge		--	8.5	--	nC
Q _{gd}	Gate-Drain Charge		--	7.5	--	nC
Switching Characteristics						
t _{d(on)}	Turn-On Time	V _{DS} = 380 V, I _D = 5.5 A, R _G = 6.8 Ω, V _{GS} = 10V	--	9	--	ns
t _r	Turn-On Rise Time		--	4	--	ns
t _{d(off)}	Turn-Off Delay Time		--	40	65	ns
t _f	Turn-Off Fall Time		--	4.5	8	ns
Source-Drain Diode Maximum Ratings and Characteristics						
I _S	Continuous Source-Drain Diode Forward Current		--	--	11.0	A
I _{SM}	Pulsed Source-Drain Diode Forward Current		--	--	33.0	
V _{SD}	Source-Drain Diode Forward Voltage	I _S = 11.0 A, V _{GS} = 0 V	--	0.9	1.2	V
t _{rr}	Reverse Recovery Time	I _S = 11.0 A	--	245	--	ns
Q _{rr}	Reverse Recovery Charge	di/dt = 100 A/μs	--	2.4	--	μC

Notes ;

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $V_{DD}=50\text{ V}, R_G=25\text{ }\Omega$, Starting $T_J=25\text{ }^{\circ}\text{C}$

Typical Characteristics

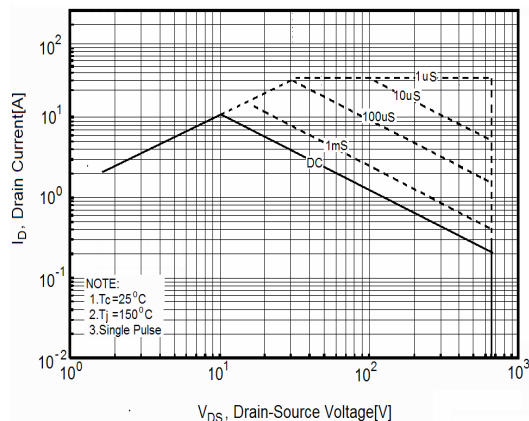


Figure 1. Safe Operating Area(TO-220)

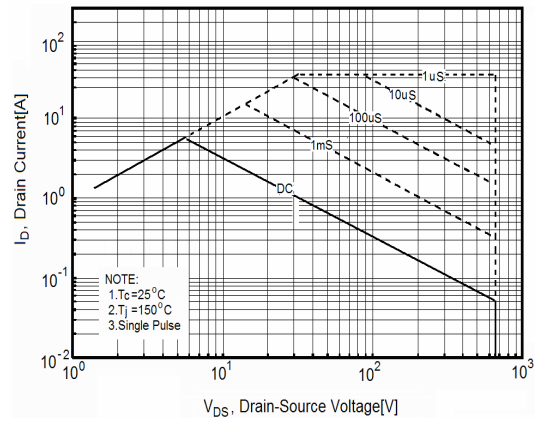


Figure 2. Safe Operating Area(TO-220F)

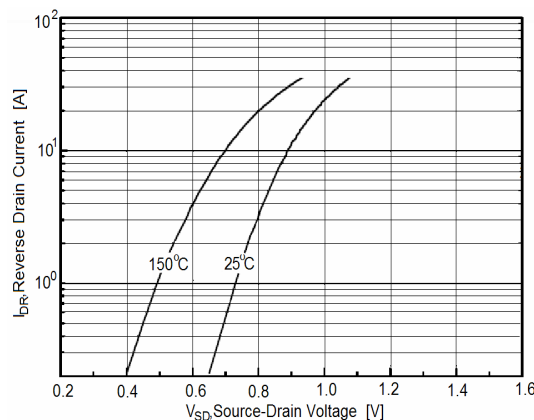


Figure 3. Source-Drain Diode Forward Voltage

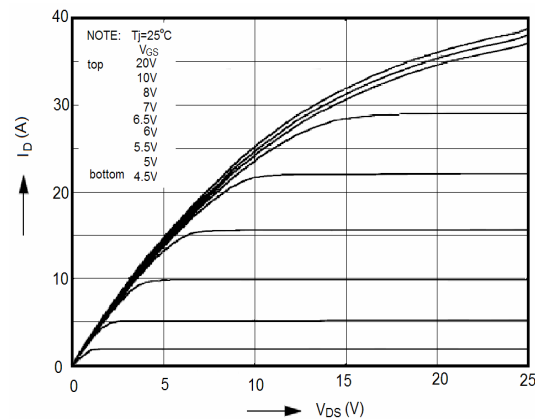


Figure 4. Output Characteristics

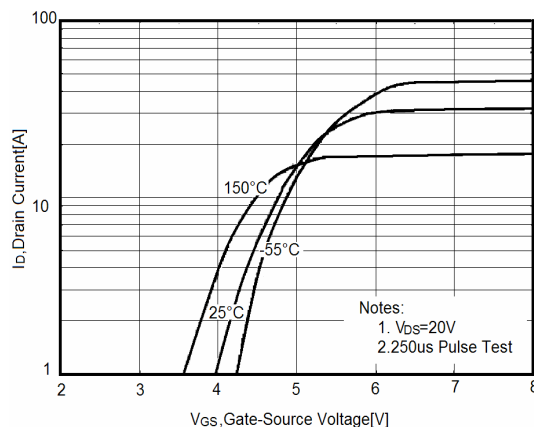


Figure 5. Transfer Characteristics

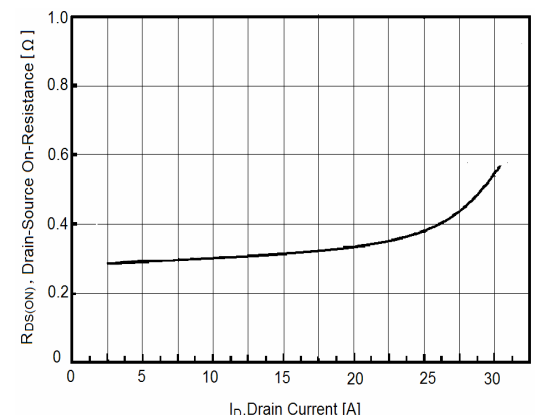


Figure 6. Static Drain-Source On Resistance

Typical Characteristics (continued)

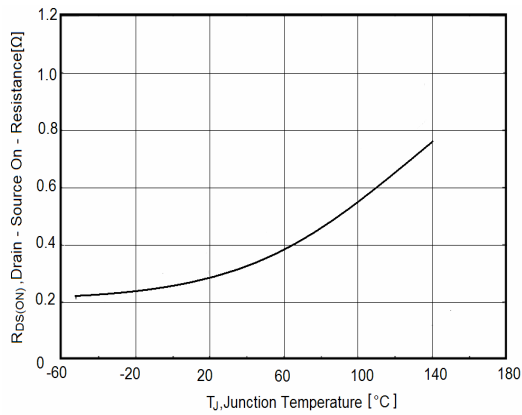


Figure 7. Rds(on) vs. Junction Temperature

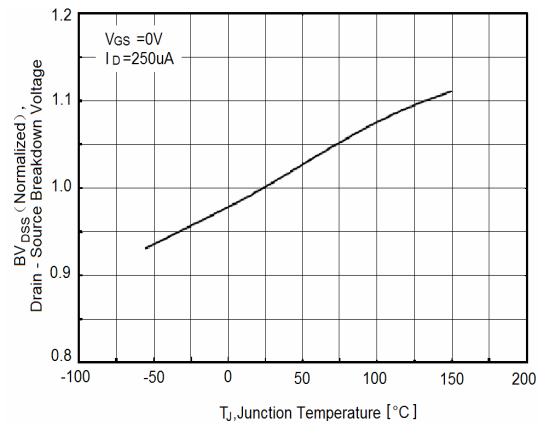


Figure 8. BVdss vs. Junction Temperature

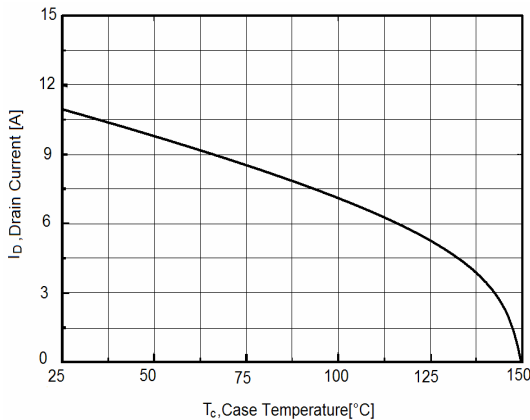


Figure 9. Maximum ID vs. Junction Temperature

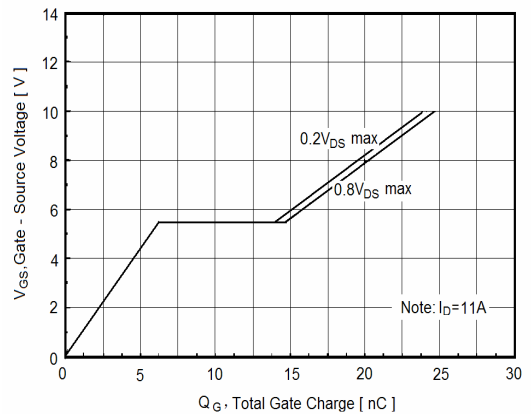


Figure 10. Gate Charge Waveforms

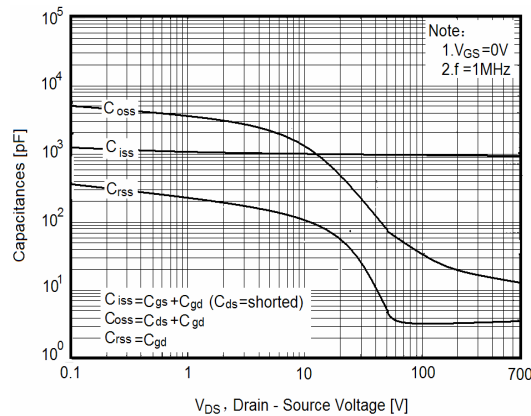


Figure 11. Capacitance

Typical Characteristics (continued)

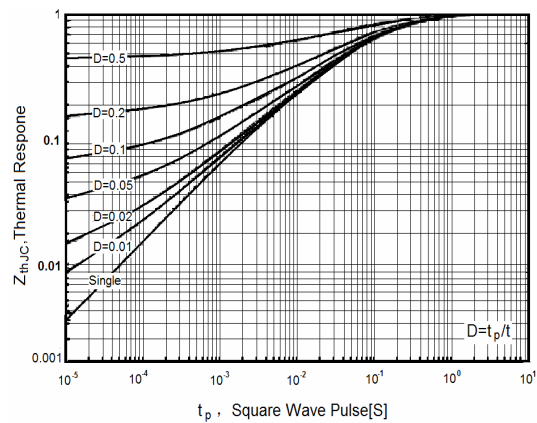


Figure 12. Transient Thermal Response Curve (TO-220)

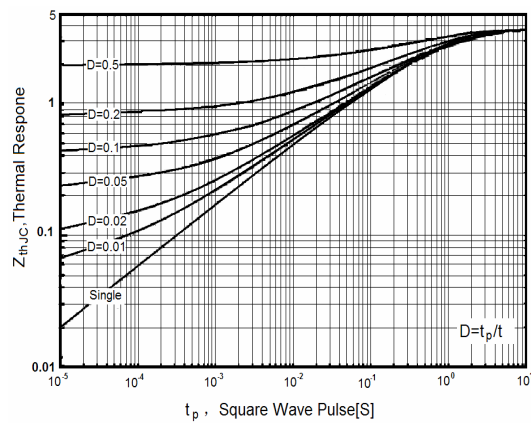
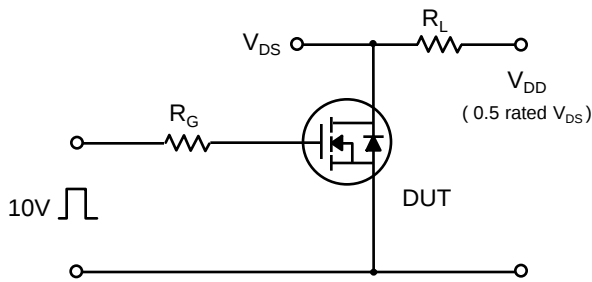
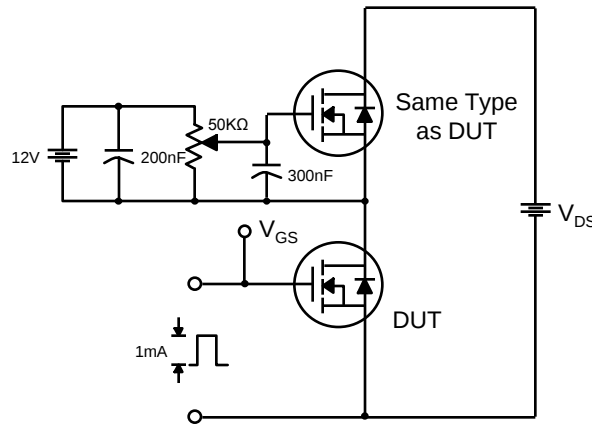


Figure 13. Transient Thermal Response Curve (TO-220F)

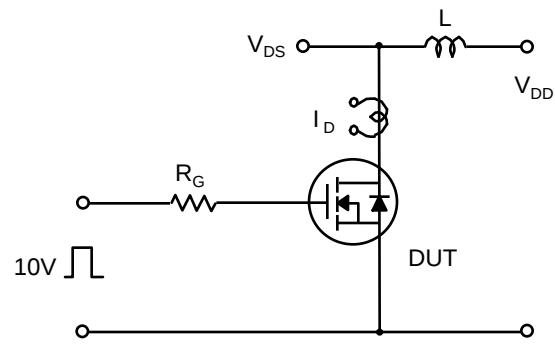
Characteristics Test Circuit & Waveform



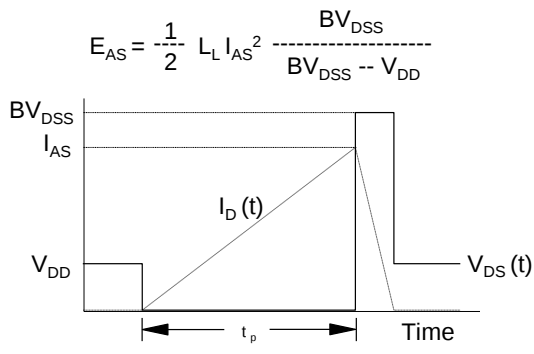
Switching Time Test Circuit & Waveforms



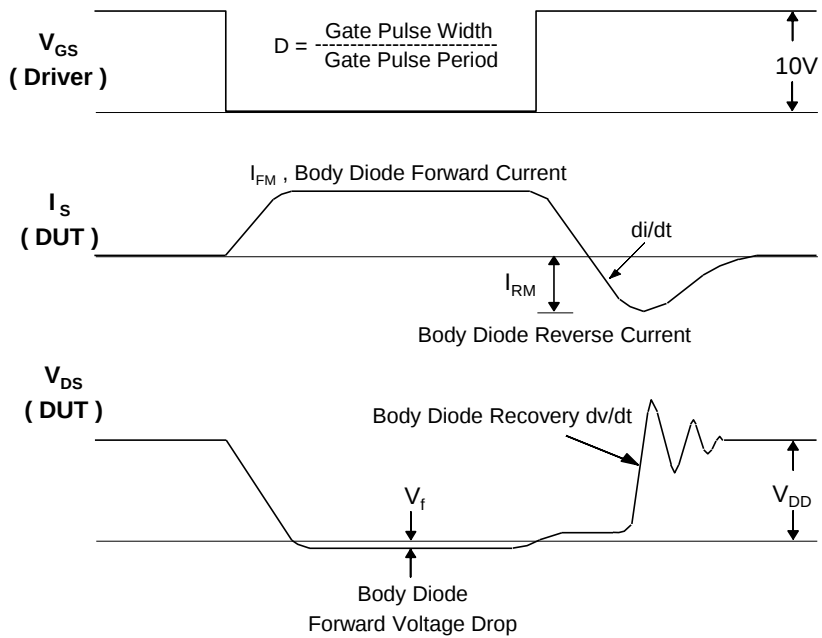
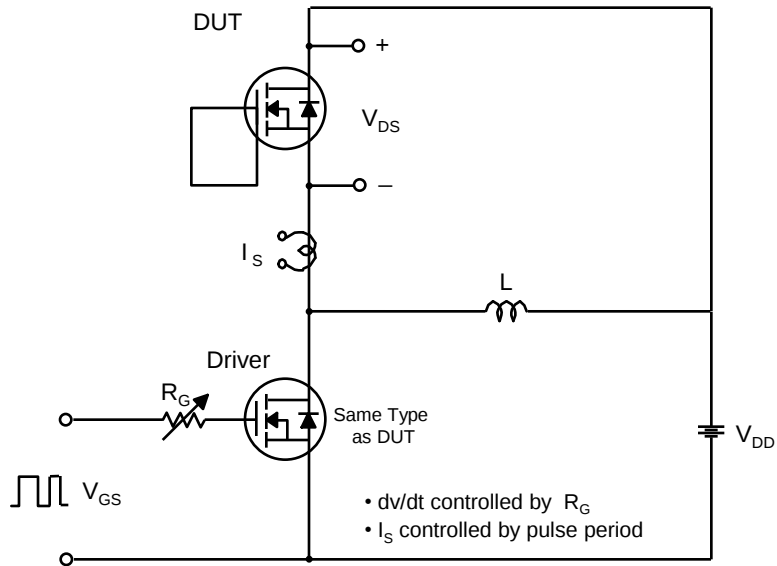
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms



Characteristics Test Circuit & Waveform (continued)



Peak Diode Recovery dv/dt Test Circuit & Waveforms